



09/988984

Cofc

Docket No.: M4065.0608/P608  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Letters Patent of:  
John T. Moore et al.

Patent No.: 6,815,818

Issued: November 9, 2004

For: ELECTRODE STRUCTURE FOR USE IN AN  
INTEGRATED CIRCUIT

**REQUEST FOR CERTIFICATE OF CORRECTION  
PURSUANT TO 37 CFR § 1.322**

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**Certificate  
MAY 15 2006  
of Correction**

Dear Sir:

Upon reviewing the above-identified patent, Patentees noted omissions and a typographical error which should be corrected.

In the **Specification**: Column 11, line 10, "for" should read --form--.

In **Item (56) (References Cited)**: The non-patent literature cited during prosecution of the application (No. 09/988,984) has not been listed. The non-patent literature was considered during prosecution. Attached are Examiner-initialed and returned copies of eight relevant pages listing 174 references from Applicants' Forms PTO/SB/08A submitted with Information Disclosure Statements dated October 16, 2002 and May 20, 2003.

The errors were not in the application as filed or amended by Applicants. Accordingly no fee is believed to be required.

**MAY 15 2006**

Transmitted herewith is a proposed Certificate of Correction effecting such corrections. Patentees respectfully solicit the granting of the requested Certificate of Correction.

Dated: May 11, 2006

Respectfully submitted,

By 

Thomas J. D'Amico

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MAY 15 2006

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Substitute for form 1449B/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 2 of 8

## Complete if Known

Application Number 09/988,984  
 Filing Date November 19, 2001  
 First Named Inventor John T. Moore  
 Group Art Unit 2812-2823  
 Examiner Name Not Yet Assigned  
 Attorney Docket Number M4065.0608/P608

## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
Tup	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
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INFORMATION DISCLOSURE  
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Sheet	3	of	8	Application Number	09/988,984
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Examiner Name	Not Yet Assigned
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Group Art Unit	2842 2823
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608

Sheet	4	of	8
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Filing Date	November 19, 2001
First Named Inventor	John T. Moore
Group Art Unit	2842 2823
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608

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Tup	CO3	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of $\text{Ag}_x(\text{GeSe}_3)_{1-x}$ ( $0 < x < 0.571$ ) glasses, Solid state Ionics 123 (1999) 259-269.	
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STATEMENT BY APPLICANT

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Sheet	7	of	8	Attorney Docket Number	M4065.0608/P608
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## Complete if Known

Application Number	09/988,984
Filing Date	November 19, 2001
First Named Inventor	John T. Moore
Group Art Unit	2012 28 23
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608

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 Sheet 8 of 8

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Group Art Unit	2842-2823
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608

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Examiner Signature	<i>Shamir</i>	Date Considered	3/2/2002
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,815,818  
DATED : November 9, 2004  
INVENTOR(S) : John T. Moore et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 11, line 10, "for" should read --form--.

Item (56) (References Cited) should include the following cited art:

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MAILING ADDRESS OF SENDER:  
Thomas J. D'Amico  
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**Item (56) (References Cited) -- continued**

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PATENT NO. 6,815,818

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**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

PATENT NO. : 6,815,818  
DATED : November 9, 2004  
INVENTOR(S) : John T. Moore et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

**Item (56) (References Cited) -- continued**

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